

L Number	Hits	Search Text	DB	Time stamp
1	55654	(silicon near oxide or "Sio.sub.2") same (remov\$3 or etch\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/04 17:24
2	1364	(silicon near oxide or "Sio.sub.2") same (oxygen near plasma)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/04 14:39
3	1148	((silicon near oxide or "Sio.sub.2") same (remov\$3 or etch\$3)) and ((silicon near oxide or "Sio.sub.2") same (oxygen near plasma))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/04 14:40
4	52	((silicon near oxide or "Sio.sub.2") same (remov\$3 or etch\$3)) and ((silicon near oxide or "Sio.sub.2") same (oxygen near plasma))) and (ion near5 (inert near gas or argon))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/04 14:41
5	16	((silicon near oxide or "Sio.sub.2") same (remov\$3 or etch\$3)) and ((silicon near oxide or "Sio.sub.2") same (oxygen near plasma))) and (ion near5 (inert near gas or argon))) and @pd<19990507	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/04 16:19
6	1894	((oxygen near plasma) or ashing) same (silicon near oxide or "Sio sub.2")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/04 16:24
7	1515	((oxygen near plasma) or ashing) same (silicon near oxide or "Sio sub.2")) same (etch\$3 or remov\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/04 16:29
8	695	((oxygen near plasma) or ashing) same (silicon near oxide or "Sio sub.2")) same (etch\$3 or remov\$3)) and @pd<19990507	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/04 16:30
9	167	((oxygen near plasma) or ashing) same (silicon near oxide or "Sio.sub.2")) same (etch\$3 or remov\$3)) and @pd<19990507) and (argon or (inert near gas))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/04 16:51
10	72	(native near oxide) same (oxygen near plasma)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/04 17:05
11	30	((native near oxide) same (oxygen near plasma)) and @pd<19990507	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/04 17:08
12	16	(silicon near oxide or "Sio.sub.2") same (remov\$3 or etch\$3) and (((native near oxide) same (oxygen near plasma)) and @pd<19990507)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/04 17:14
13	7	(silicon near oxide or "Sio.sub.2") same (remov\$3 or etch\$3) and (((native near oxide) same (oxygen near plasma)) and @pd<19990507) and argon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/04 17:15

14	324	((silicon near oxide or "Sio.sub.2") same (remov\$3 or etch\$3 or clean\$3) and 134/1.1-1.3.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/04 17:27
15	117	((silicon near oxide or "Sio.sub.2") same (remov\$3 or etch\$3 or clean\$3) and 134/1.1-1.3.ccls.) and (ion near argon or "Ar"or sputter\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/04 17:30
16	52	((silicon near oxide or "Sio.sub.2") same (remov\$3 or etch\$3 or clean\$3) and 134/1.1-1.3.ccls.) and (ion near argon or "Ar"or sputter\$3)) and @pd<19990507	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/04 17:34
17	2	((silicon near oxide or "Sio.sub.2") same (remov\$3 or etch\$3 or clean\$3) and 134/1.1-1.3.ccls.) and (ion near argon or "Ar"or sputter\$3)) and @pd<19990507 and ((silicon near oxide or "Sio.sub.2") same (oxygen near plasma))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/04 17:36
18	31	((silicon near oxide or "Sio.sub.2") same (remov\$3 or etch\$3)) and ((silicon near oxide or "Sio.sub.2") same (oxygen near plasma))) and 438/723.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/04 17:37
19	11	((silicon near oxide or "Sio.sub.2") same (remov\$3 or etch\$3)) and ((silicon near oxide or "Sio.sub.2") same (oxygen near plasma))) and 438/723.ccls.) and @pd<19990507	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/04 17:38